

PLEASE AMEND THE CLAIMS AS FOLLOWS:

Claim 19. (previously amended) A cylindrical shaped, capacitor

structure, featuring a cylindrical storage node

structure comprised of an underlying, uniformly doped,

cylindrical polysilicon shape and an overlying

5       agglomerated metal silicide layer, wherein said

agglomerated metal silicide layer is located only on

exposed surfaces of said cylindrical polysilicon shape,

comprising:

      said cylindrical polysilicon shape comprised of a

10      bottom polysilicon shape located on a first section of a

top surface of an underlying planar, insulator layer, with

said bottom polysilicon shape overlying and contacting a

top surface of a plug structure which in turn is located

in an opening in said insulator layer, and with said

15      cylindrical polysilicon shape comprised of uniformly

doped, vertical polysilicon shapes, located overlying

second sections of said planar, insulator layer, with

bottom portions of said vertical polysilicon shapes

butting edges of said bottom polysilicon shape;

said agglomerated metal silicide layer with a roughened top surface, located only on exposed portions of said cylindrical polysilicon shape ~~shaped storage node~~ and not located on any other surface of said cylindrical shaped, 5 capacitor structure or on any surface of said planar insulator layer, with ~~said and featuring~~ agglomerated metal silicide on top surface of said bottom polysilicon shape, and on all surfaces of uniformly doped, said vertical polysilicon shapes, resulting in said cylindrical shape 10 storage node structure comprised of with said agglomerated metal silicide layer located only on said cylindrical polysilicon shape;

    a capacitor dielectric layer located only on the exposed surfaces of said cylindrical polysilicon shape 15 ~~storage node structure~~, with said capacitor dielectric layer located only overlying said agglomerated metal silicide layer; and

    an upper electrode, covering said capacitor dielectric layer.

Claim 20 (cancelled)

TSMC97-232BC

Claim 21 (currently amended) The semiconductor cylindrical shaped, capacitor structure of Claim 19, wherein said agglomerated metal silicide layer is selected from a group consisting of titanium silicide, cobalt silicide, nickel silicide, and platinum silicide.